



CMLT2207
CMLT2207G

SURFACE MOUNT
PICOmini™
DUAL, COMPLEMENTARY
SILICON TRANSISTORS

PICOmini™



SOT-563 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLT2207 and CMLT2207G each consist of one isolated 2N2222A NPN transistor and one complementary isolated 2N2907A PNP transistor, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This PICOmini™ device has been designed for small signal general purpose amplifier and switching applications.

- The CMLT2207G is **Halogen Free** by design.

MARKING CODES:

CMLT2207: L70

CMLT2207G: L7G

MAXIMUM RATINGS: (T_A=25°C)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	NPN (Q1)	PNP (Q2)	UNITS
V _{CBO}	75	60	V
V _{CEO}	40	60	V
V _{EBO}	6.0	5.0	V
I _C	600		mA
P _D	350		mW
T _J , T _{stg}	-65 to +150		°C
θ _{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

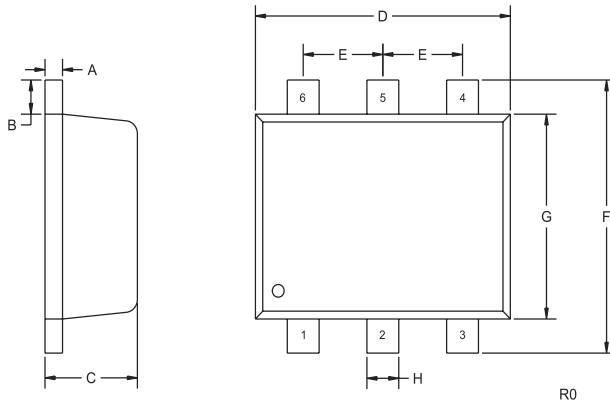
SYMBOL	TEST CONDITIONS	NPN (Q1)		PNP (Q2)		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =60V	-	10	-	-	nA
I _{CBO}	V _{CB} =50V	-	-	-	10	nA
I _{CBO}	V _{CB} =60V, T _A =125°C	-	10	-	-	nA
I _{CBO}	V _{CB} =50V, T _A =125°C	-	-	-	10	nA
I _{EBO}	V _{EB} =3.0V	-	10	-	-	nA
I _{CEV}	V _{CE} =60V, V _{EB(OFF)} =3.0V	-	10	-	-	nA
I _{CEV}	V _{CE} =30V, V _{EB(OFF)} =500mV	-	-	-	50	nA
BV _{CBO}	I _C =10μA	75	-	60	-	V
BV _{CEO}	I _C =10mA	40	-	60	-	V
BV _{EBO}	I _E =10μA	6.0	-	5.0	-	V
V _{CE(SAT)}	I _C =150mA, I _B =15mA	-	0.3	-	0.4	V
V _{CE(SAT)}	I _C =500mA, I _B =50mA	-	1.0	-	1.6	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA	0.6	1.2	-	1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA	-	2.0	-	2.6	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	35	-	75	-	
h _{FE}	V _{CE} =10V, I _C =1.0mA	50	-	100	-	
h _{FE}	V _{CE} =10V, I _C =10mA	75	-	100	-	
h _{FE}	V _{CE} =10V, I _C =150mA	100	300	100	300	
h _{FE}	V _{CE} =1.0V, I _C =150mA	50	-	-	-	
h _{FE}	V _{CE} =10V, I _C =500mA	40	-	50	-	

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ELECTRICAL CHARACTERISTICS - Continued:

SYMBOL	TEST CONDITIONS	NPN (Q1)		PNP (Q2)		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	300	-	-	-	MHz
f_T	$V_{CE}=20V, I_C=50mA, f=100MHz$	-	-	200	-	MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$	-	8.0	-	8.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$	-	25	-	-	pF
C_{ib}	$V_{EB}=2.0V, I_C=0, f=1.0MHz$	-	-	-	30	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	2.0	8.0	-	-	k Ω
h_{ie}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	0.25	1.25	-	-	k Ω
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	-	8.0	-	-	x10-4
h_{re}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	-	4.0	-	-	x10-4
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	300	-	-	
h_{fe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	75	375	-	-	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	5.0	35	-	-	μS
h_{oe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	25	200	-	-	μS
rb/C_c	$V_{CB}=10V, I_E=20mA, f=31.8MHz$	-	150	-	-	ps
NF	$V_{CE}=10V, I_C=100\mu A, R_S=1.0k\Omega, f=1.0kHz$	-	4.0	-	-	dB
t_{on}	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$	-	-	-	45	ns
t_d	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$	-	10	-	10	ns
t_r	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$	-	25	-	40	ns
t_{off}	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$	-	-	-	100	ns
t_s	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$	-	225	-	-	ns
t_s	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$	-	-	-	80	ns
t_f	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$	-	60	-	-	ns
t_f	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$	-	-	-	30	ns

SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS		MIN	MAX
	INCHES	MILLIMETERS		
A	0.004	0.007	0.10	0.18
B	0.008	0.20		
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020	0.50		
F	0.061	0.067	1.55	1.70
G	0.047	1.20		
H	0.006	0.012	0.15	0.30

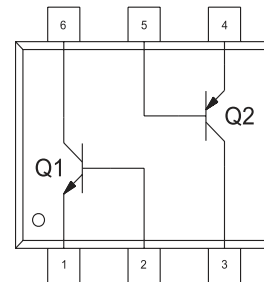
SOT-563 (REV: R0)

MARKING CODES:

CMLT2207: L70
CMLT2207G: L7G

LEAD CODE:

- 1) EMITTER Q1
- 2) BASE Q1
- 3) COLLECTOR Q2
- 4) EMITTER Q2
- 5) BASE Q2
- 6) COLLECTOR Q1



R2 (6-June 2008)